Octal 3-State Noninverting Bus Transceiver with LSTTL-Compatible Inputs

High-Performance Silicon-Gate CMOS

The 74HCT245 is identical in pinout to LS245. The device has TTL-Compatible Inputs.

The HCT245 is a 3-state noninverting transceiver that is used for 2-way asynchronous communication between data buses. The device has an active-low Output Enable pin, which is used to place the I/O ports into high-impedance states. The Direction control determines whether data flows from A to B or from B to A.

Features

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 308 FETs or 77 Equivalent Gates
- This is a Pb-Free Device



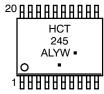
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



TSSOP-20 DT SUFFIX CASE 948E



HCT245 = Device Code

A = Assembly Location

L = Wafer Lot
Y = Year
W = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

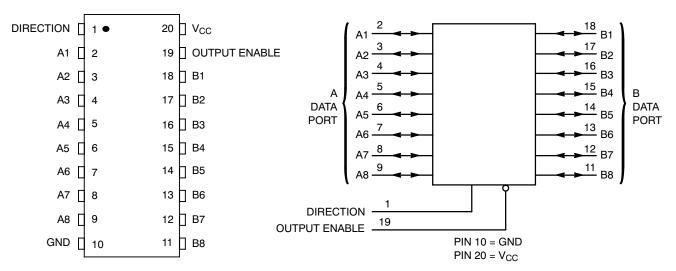


Figure 1. Pin Assignment

Figure 2. Logic Diagram

FUNCTION TABLE

Control Inputs			
Output Enable Direction		Operation	
L	L	Data Transmitted from Bus B to Bus A	
L	Н	Data Transmitted from Bus A to Bus B	
Н	Х	Buses Isolated (High-Impedance State)	

X = don't care

ORDERING INFORMATION

Device	Package	Shipping [†]
74HCT245DTR2G	TSSOP-20*	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb-Free.

MAXIMUM RATINGS (Note 1)

Symbol	F	Parameter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to V _{CC} +0.5	V
V _{OUT}	DC Output Voltage	(Note 2)	-0.5 to $V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current		±20	mA
I _{OK}	DC Output Diode Current		±35	mA
I _{OUT}	DC Output Sink Current		±35	mA
I _{CC}	DC Supply Current per Supply Pin		±75	mA
I _{GND}	DC Ground Current per Ground Pin		±75	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias		+ 150	°C
$\theta_{\sf JA}$	Thermal Resistance	TSSOP	128	°C/W
P_{D}	Power Dissipation in Still Air at 85°C	TSSOP	450	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% to 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4)	> 2000 > 200	V
ILATCHUP	Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 5)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 20 ounce copper trace with no air flow.

- I_O absolute maximum rating must observed.
 Tested to EIA/JESD22-A114-A.
- 4. Tested to EIA/JESD22-A115-A.
- Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 3) V _{CC} = 4.5 V	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Vcc	Guaranteed Limit			
Symbol	Parameter	Condition		(V)	-55 to 25°C	≤85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1V$ $ I_{out} \le 20\mu A$		4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = V_{CC} - 0.1$ $ I_{out} \le 20\mu A$	IV	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20\mu A$		4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		V _{in} = V _{IL}	$ I_{out} \le 4.0 \text{mA}$	4.5	3.98	3.84	3.70	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20\mu A$		4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		V _{in} = V _{IH}	$ I_{out} \le 4.0 \text{mA}$	4.5	0.26	0.33	0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND		5.5	±0.1	±1.0	±1.0	μΑ
I _{OZ}	Maximum Three-State Leakage Current	Output in High- In V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GN		5.5	±0.5	±5.0	±10	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GN I _{out} = 0μA	ID	5.5	4.0	40	40	μΑ
ΔI_{CC}	Additional Quiescent Supply	V _{in} = 2.4V, Any One Input V _{in} = V _{CC} or GND, Other Inputs			≥ -55°C	25 to	125°C	
<u> </u>	Garront	$I_{out} = 0\mu A$	D, Other Inputs	5.5	2.9	2	.4	mA

^{6.} Information on typical parametric values can be found in Chapter 2the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

			Guaranteed Limit			
Symbol	Parameter	V _{CC} V	–55 to 25°C	≤ 85 ° C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to B, B to A (Figures 1 and 3)	4.5	15	19	22	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Direction or Output Enable to A or B (Figures 2 and 4)	4.5	22	28	33	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to A or B (Figures 2 and 4)	4.5	22	28	33	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	4.5	12	15	18	ns
C _{in}	Maximum Input Capacitance (Pin 1 or Pin 19)	-	10	10	10	pF
C _{out}	Maximum Three-State I/O Capacitance (I/O in High-Impedance State)	-	15	15	15	pF

^{8.} For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High- Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C_PD	Power Dissipation Capacitance (Per Transceiver Channel) (Note 9)	40	pF

^{9.} Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

^{7.} Total Supply Current = $I_{CC} + \Sigma \Delta I_{CC}$.

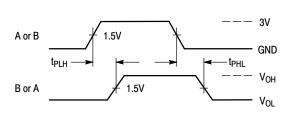


Figure 3. Switching Waveform

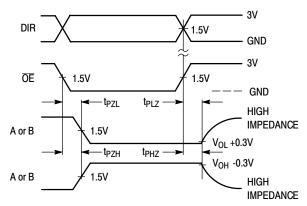
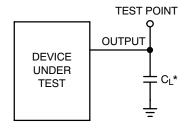
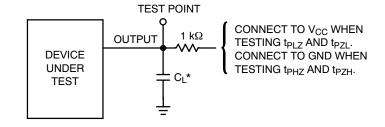


Figure 4. Switching Waveform





^{*}Includes all probe and jig capacitance

*Includes all probe and jig capacitance

Figure 5. Test Circuit

Figure 6. Test Circuit

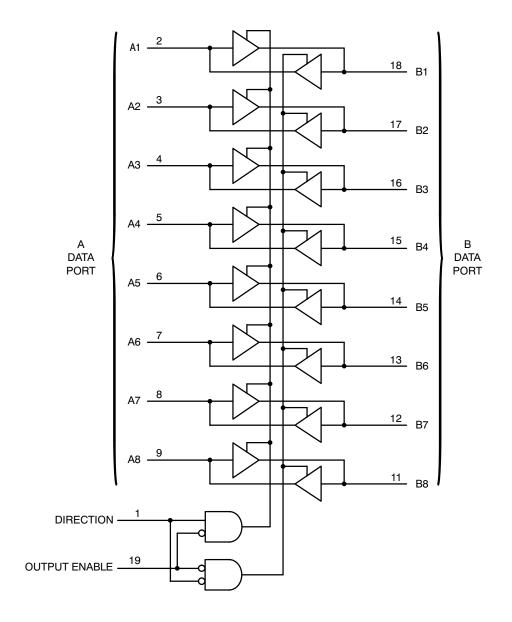
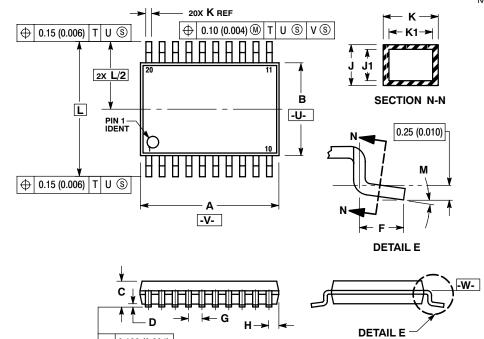


Figure 7. Expanded Logic Diagram

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 **ISSUE C**



0.100 (0.004) -T- SEATING PLANE

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES			
DIM	MIN	MAX	MIN	MAX			
Α	6.40	6.60	0.252	0.260			
В	4.30	4.50	0.169	0.177			
С		1.20		0.047			
D	0.05	0.15	0.002	0.006			
F	0.50	0.75	0.020	0.030			
G	0.65	BSC	0.026 BSC				
Н	0.27	0.37	0.011	0.015			
J	0.09	0.20	0.004	0.008			
J1	0.09	0.16	0.004	0.006			
K	0.19	0.30	0.007	0.012			
K1	0.19	0.25	0.007	0.010			
٦	6.40	BSC	0.252 BSC				
М	0°	8°	0°	8°			

SOLDERING FOOTPRINT* - 7.06 0.65 **PITCH** 16X 16X

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DIMENSIONS: MILLIMETERS

1.26

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